

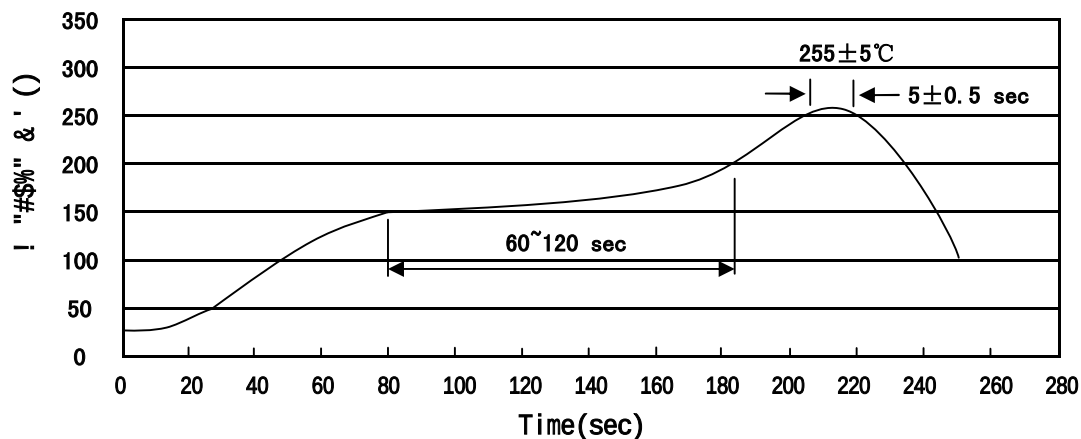
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SOT-23 N MOS N-CHANNEL MOSFET in a SOT-23 Plastic Package.

Low $R_{DS(on)}$, rugged and reliable, compact industry standard SOT-23 surface mount package

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current	I_D	220	mA
Peak Drain Current	I_{DM}	880	mA
Power Dissipation	P_D	360	mW
Thermal Resistance, Junction-to-			

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

Note:

- 1、预热温度 150 ~ 200 °C，时间 60 ~ 120sec; 1.Preheating:150~200°C, Time:60~120sec.
- 2、峰值温度 255±5 °C，时间持续为 5±0.5sec; 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
- 3、焊接制程冷却速度为 2 ~ 10°C/sec. 3. Cooling Speed: 2~10°C/sec.

/ Resistance to Soldering Heat Test Conditions

温度：260±5°C 时间：10±1 sec. Temp.:260±5°C Time:10±1 sec

/ Packaging SPEC.

卷盘包装 / REEL

Package Type	Units " # \$					Dimension " % & (unit ' mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box (	Outer Box)
SOT-23	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

/ Notices